## SONY

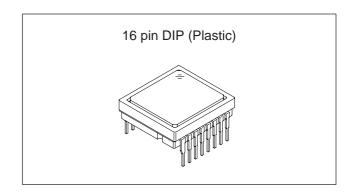
# ICX259AL

## Diagonal 6mm (Type 1/3) CCD Image Sensor for CCIR B/W Video Cameras

#### **Description**

The ICX259AL is an interline CCD solid-state image sensor suitable for CCIR B/W video cameras with a diagonal 6mm (Type 1/3) system. Compared with the current product ICX059CL, basic characteristics such as sensitivity, smear, dynamic range and S/N are improved drastically from visible light region to near infrared light region through the adoption of EXview HAD CCD<sup>TM</sup> technology.

This chip features a field period readout system and an electronic shutter with variable charge-storage time.

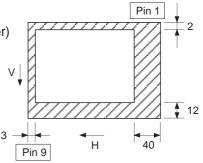


#### **Features**

- Sensitivity in near infrared light region (+8dB compared with the ICX059CL, λ = 945nm)
- High sensitivity (+7dB compared with the ICX059CL, no IR cut filter)
- Low smear (-20dB compared with the ICX059CL)
- High D range (+5dB compared with the ICX059CL)
- High S/N
- High resolution and low dark current
- Excellent antiblooming characteristics
- Continuous variable-speed shutter
- No voltage adjustment

(Reset gate and substrate bias are not adjusted.)

Reset gate: 5V driveHorizontal register: 5V drive



Optical black position (Top View)

#### **Device Structure**

• Interline CCD image sensor

• Image size: Diagonal 6mm (Type 1/3)

Number of effective pixels: 752 (H) × 582 (V) approx. 440K pixels
 Total number of pixels: 795 (H) × 596 (V) approx. 470K pixels

• Chip size: 6.00mm (H)  $\times$  4.96mm (V) • Unit cell size: 6.50 $\mu$ m (H)  $\times$  6.25 $\mu$ m (V)

• Optical black: Horizontal (H) direction: Front 3 pixels, rear 40 pixels

Vertical (V) direction : Front 12 pixels, rear 2 pixels

Number of dummy bits: Horizontal 22

Vertical 1 (even fields only)

Substrate material: Silicon

## **EXview HAD CCD**<sub>TM</sub>

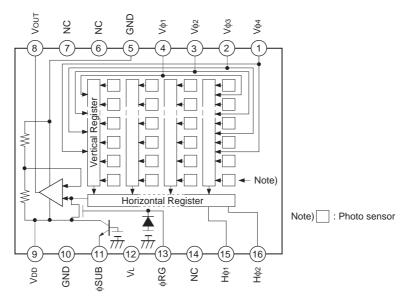
\* EXview HAD CCD is a trademark of Sony Corporation.

EXview HAD CCD is a CCD that drastically improves light efficiency by including near infrared light region as a basic structure of HAD (Hole-Accumulation-Diode) sensor.

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## **Block Diagram and Pin Configuration**

(Top View)



## **Pin Description**

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	Vф4	Vertical register transfer clock	9	VDD	Supply voltage
2	Vфз	Vertical register transfer clock	10	GND	GND
3	Vф2	Vertical register transfer clock	11	φSUB	Substrate clock
4	Vф1	Vertical register transfer clock	12	VL	Protective transistor bias
5	GND	GND	13	φRG	Reset gate clock
6	NC		14	NC	
7	NC		15	Нф1	Horizontal register transfer clock
8	Vouт	Signal output	16	Нф2	Horizontal register transfer clock

## **Absolute Maximum Ratings**

	Item	Ratings	Unit	Remarks
	Vdd, Vout, фRG – фSUB	-40 to +8	V	
Against &CLID	Vφ1, Vφ3 – φSUB	-50 to +15	V	
Against φSUB	Vφ2, Vφ4, VL – φSUB	-50 to +0.3	V	
	Hφ1, Hφ2, GND – φSUB	-40 to +0.3	V	
	Vdd, Vout, фRG – GND	-0.3 to +20	V	
Against GND	Vφ1, Vφ2, Vφ3, Vφ4 – GND	-10 to +18	V	
	Hφ1, Hφ2 – GND	-10 to +6	V	
Against V	Vφ1, Vφ3 – VL	-0.3 to +28	V	
Against V∟	Vφ2, Vφ4, Hφ1, Hφ2, GND – VL	-0.3 to +15	V	
	Voltage difference between vertical clock input pins	to +15	V	*1
Between input clock pins	Ηφ1 – Ηφ2	-6 to +6	V	
F	Ηφ1, Ηφ2 – Vφ4	-14 to +14	V	
Storage temperature		-30 to +80	°C	
Operating temperature	-10 to +60	°C		

<sup>\*1 +24</sup>V (Max.) when clock width < 10 $\mu$ s, clock duty factor < 0.1%. -2-

## **Bias Conditions**

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply voltage	VDD	14.55	15.0	15.45	V	
Protective transistor bias	VL		*1			
Substrate clock	φSUB		*2			
Reset gate clock	φRG		*2			

<sup>\*1</sup> VL setting is the VvL voltage of the vertical transfer clock waveform, or the same power supply as the VL power supply for the V driver should be used.

## **DC Characteristics**

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply current	IDD		4	6	mA	

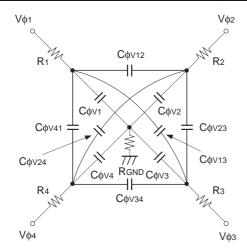
## **Clock Voltage Conditions**

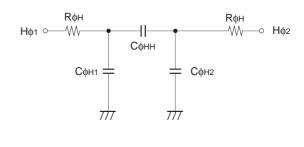
Item	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Readout clock voltage	VvT	14.55	15.0	15.45	V	1	
	VvH1, VvH2	-0.05	0	0.05	V	2	VvH = (VvH1 + VvH2)/2
	VvH3, VvH4	-0.2	0	0.05	V	2	
	VVL1, VVL2, VVL3, VVL4	-8.0	-7.0	-6.5	V	2	VvL = (VvL3 + VvL4)/2
	Vφv	6.3	7.0	8.05	V	2	$V \phi V = V V H N - V V L N (N = 1 to 4)$
Vertical transfer clock	VvH3 — VvH	-0.25		0.1	V	2	
voltage	VvH4 — VvH	-0.25		0.1	V	2	
	Vvhh			0.3	V	2	High-level coupling
	VvhL			0.3	V	2	High-level coupling
	Vvlh			0.3	V	2	Low-level coupling
	VVLL			0.3	V	2	Low-level coupling
Horizontal transfer	Vфн	4.75	5.0	5.25	V	3	
clock voltage	VHL	-0.05	0	0.05	V	3	
Reset gate clock	Vørg	4.5	5.0	5.5	V	4	Input through 0.1µF capacitance
voltage	VRGLH – VRGLL			0.4	V	4	Low-level coupling
	VRGL - VRGLm			0.5	V	4	Low-level coupling
Substrate clock voltage	Vфѕив	21.0	22.0	23.5	V	5	

<sup>\*2</sup> Do not apply a DC bias to the substrate clock and reset gate clock pins, because a DC bias is generated within the CCD.

## **Clock Equivalent Circuit Constant**

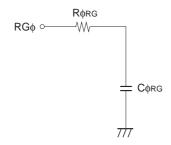
Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Capacitance between vertical transfer	Сфу1, Сфуз		1200		pF	
clock and GND	Сф∨2, Сф∨4		1000		pF	
	Сф∨12, Сф∨34		680		pF	
Capacitance between vertical transfer	Сф∨23, Сф∨41		330		pF	
clocks	Сф∨13		100		pF	
	Сф∨24		100		pF	
Capacitance between horizontal transfer clock and GND	Сфн1, Сфн2		75		pF	
Capacitance between horizontal transfer clocks	Сфнн		30		pF	
Capacitance between reset gate clock and GND	Сфяс		5		pF	
Capacitance between substrate clock and GND	Сфѕив		270		pF	
Variable transfer plants or size and inter-	R1, R3		82		Ω	
Vertical transfer clock series resistor	R2, R4		120		Ω	
Vertical transfer clock ground resistor	RGND		100		Ω	
Horizontal transfer clock series resistor	Rфн		15		Ω	
Reset gate clock series resistor	Rørg		50		Ω	





Vertical transfer clock equivalent circuit

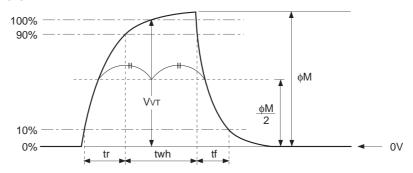
Horizontal transfer clock equivalent circuit



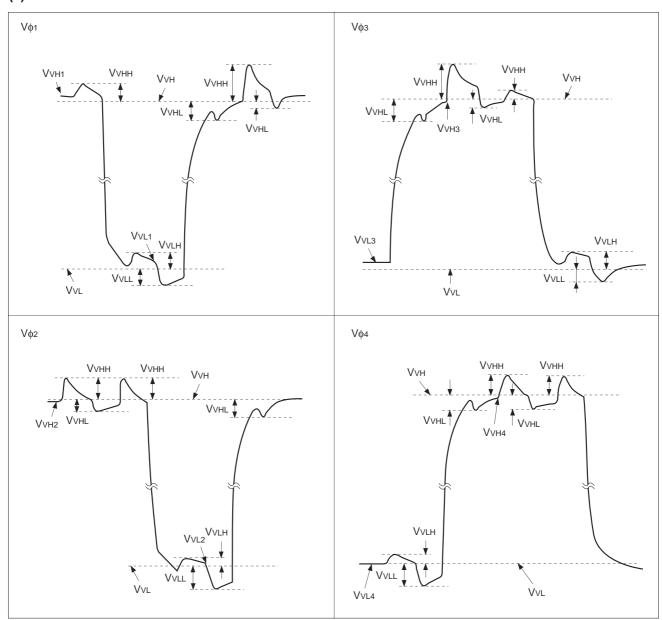
Reset gate clock equivalent circuit

## **Drive Clock Waveform Conditions**

## (1) Readout clock waveform



## (2) Vertical transfer clock waveform

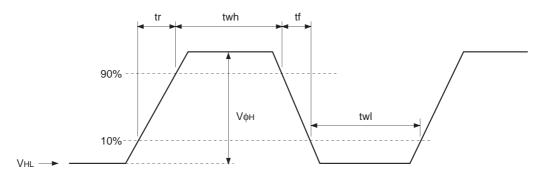


VvH = (VvH1 + VvH2)/2

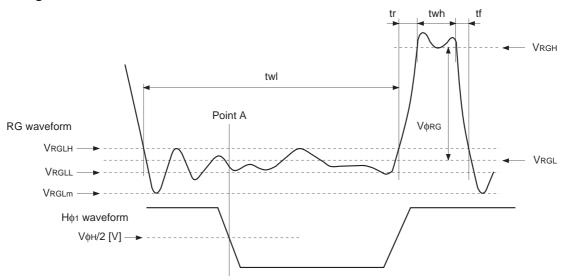
VvL = (VvL3 + VvL4)/2

 $V\phi V = VVHN - VVLN (n = 1 to 4)$ 

## (3) Horizontal transfer clock waveform



## (4) Reset gate clock waveform



VRGLH is the maximum value and VRGLL is the minimum value of the coupling waveform during the period from Point A in the above diagram until the rising edge of RG. In addition, VRGL is the average value of VRGLH and VRGLL.

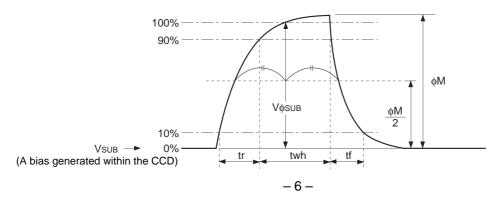
$$V_{RGL} = (V_{RGLH} + V_{RGLL})/2$$

Assuming VRGH is the minimum value during the interval twh, then:

$$V \phi RG = V RGH - V RGL$$

Negative overshoot level during the falling edge of RG is VRGLm.

## (5) Substrate clock waveform



## **Clock Switching Characteristics**

	Item	Symbol		twh			twl			tr			tf		Unit	Remarks
	пеш	Symbol	Min.	Тур.	Мах.	Min.	Тур.	Max.	Min.	Тур.	Мах.	Min.	Тур.	Max.	Offic	Remarks
Rea	dout clock	VT	2.3	2.5						0.5			0.5		μs	During readout
Vert cloc	ical transfer k	Vφ1, Vφ2, Vφ3, Vφ4										15		250	ns	*1
_ <u>\$</u>	During	Нф1	26	28.5		26	28.5			6.5	9.5		6.5	9.5	ns	*2
onta r clc	imaging	Нф2	26	28.5		26	28.5			6.5	9.5		6.5	9.5	113	
Horizontal transfer clock	During parallel-serial	Нф1		5.38						0.01			0.01		μs	
ta T	conversion	Нф2					5.38			0.01			0.01		μο	
Res	et gate clock	φRG	11	13			51			3			3		ns	
Sub	strate clock	φSUB	1.5	1.8							0.5			0.5	μs	During drain charge

<sup>\*1</sup> When vertical transfer clock driver CXD1267AN is used.

<sup>\*2</sup> tf  $\geq$  tr - 2ns, and the cross-point voltage (VcR) for the H $\phi$ 1 rising side of the H $\phi$ 1 and H $\phi$ 2 waveforms must be at least V $\phi$ H/2 [V].

Item	Symbol		two	Unit	Pomarke		
item	Symbol	Min.	Тур.	Max.	Offic	Remarks	
Horizontal transfer clock	<b>Н</b> ф1, <b>Н</b> ф2	22	26		ns	*3	

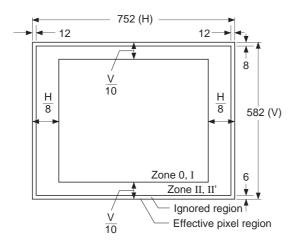
<sup>\*3</sup> The overlap period for twh and twl of horizontal transfer clocks  $H\phi_1$  and  $H\phi_2$  is two.

## **Image Sensor Characteristics**

(Ta = 25°C)

Item	Symbol	Min.	Тур.	Max.	Unit	Measurement method	Remarks
Sensitivity 1	S1	720	1000		mV	1	
Sensitivity 2	S2	2200	3200		mV	2	
Saturation signal	Vsat	1000			mV	3	Ta = 60°C
Smear	Sm		-115	-98	dB	4	
Video signal shading	SH			20	%	5	Zone 0 and I
Video signal snading	ЗП			25	%	5	Zone 0 to II'
Dark signal	Vdt			2	mV	6	Ta = 60°C
Dark signal shading	ΔVdt			1	mV	7	Ta = 60°C
Flicker	F			2	%	8	
Lag	Lag			0.5	%	9	

## **Zone Definition of Video Signal Shading**



0

### **Image Sensor Characteristics Measurement Method**

#### Measurement conditions

- 1) In the following measurements, the device drive conditions are at the typical values of the bias and clock voltage conditions.
- 2) In the following measurements, spot blemishes are excluded and, unless otherwise specified, the optical black (OB) level is used as the reference for the signal output, and the value measured at point [\*A] in the drive circuit example is used.

## **Definition of standard imaging conditions**

1) Standard imaging condition I:

Use a pattern box (luminance: 706cd/m², color temperature of 3200K halogen source) as a subject. (Pattern for evaluation is not applicable.) Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter and image at F8. The luminous intensity to the sensor receiving surface at this point is defined as the standard sensitivity testing luminous intensity.

2) Standard imaging condition II:

Indicate the state which removes an IR cut filter of standard imaging condition I.

3) Standard imaging condition III:

Image a light source (color temperature of 3200K) with a uniformity of brightness within 2% at all angles. Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.

1. Sensitivity 1

Set to standard imaging condition I. After selecting the electronic shutter mode with a shutter speed of 1/250s, measure the signal output (Vs<sub>1</sub>) at the center of the screen and substitute the value into the following formula.

2. Sensitivity 2

Set to standard imaging condition II. After selecting the electronic shutter mode with a shutter speed of 1/1000s, measure the signal output (Vs<sub>2</sub>) at the center of the screen and substitute the value into the following formula.

3. Saturation signal

Set to standard imaging condition III. After adjusting the luminous intensity to 10 times the intensity with the average value of the signal output, 200mV, measure the minimum value of the signal output.

4. Smear

Set to standard imaging condition III. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity to 500 times the intensity with the average value of the signal output, 200mV. When the readout clock is stopped and the charge drain is executed by the electronic shutter at the respective H blankings, measure the maximum value (VSm [mV]) of the signal output and substitute the value into the following formula.

Sm = 
$$20 \times log \left( \frac{YSm}{200} \times \frac{1}{500} \times \frac{1}{10} \right)$$
 [dB] (1/10V method conversion value)

#### 5. Video signal shading

Set to standard imaging condition III. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity so that the average value of the signal output is 200mV. Then measure the maximum (Vmax [mV]) and minimum (Vmin [mV]) values of the signal output and substitute the values into the following formula.

$$SH = (Vmax - Vmin)/200 \times 100 [\%]$$

#### 6. Dark signal

Measure the average value of the signal output (Vdt [mV]) with the device ambient temperature 60°C and the device in the light-obstructed state, using the horizontal idle transfer level as a reference.

#### 7. Dark signal shading

After measuring 6, measure the maximum (Vdmax [mV]) and minimum (Vdmin [mV]) values of the dark signal output and substitute the values into the following formula.

$$\Delta Vdt = Vdmax - Vdmin [mV]$$

#### 8. Flicker

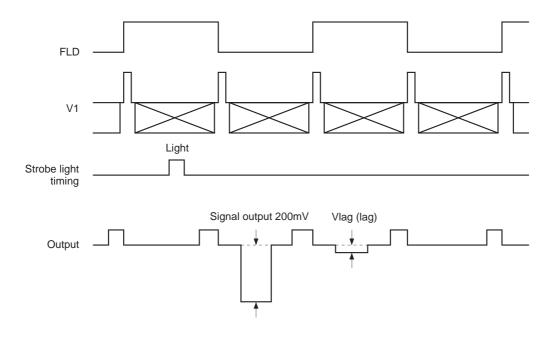
Set to standard imaging condition III. Adjust the luminous intensity so that the average value of the signal output is 200mV, and then measure the difference in the signal level between fields ( $\Delta$ Vf [mV]). Then substitute the value into the following formula.

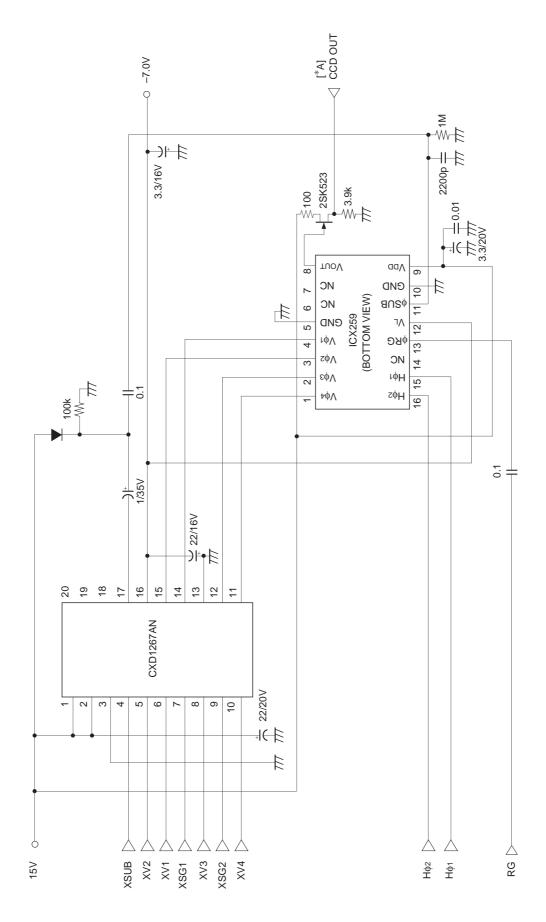
$$F = (\Delta Vf/200) \times 100 [\%]$$

#### 9. Lag

Adjust the signal output value generated by strobe light to 200mV. After setting the strobe light so that it strobes with the following timing, measure the residual signal (Vlag). Substitute the value into the following formula.

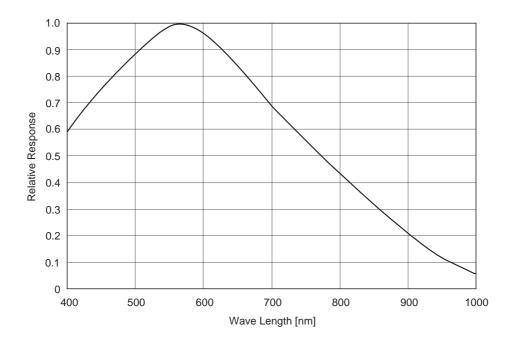
$$Lag = (Vlag/200) \times 100 [\%]$$



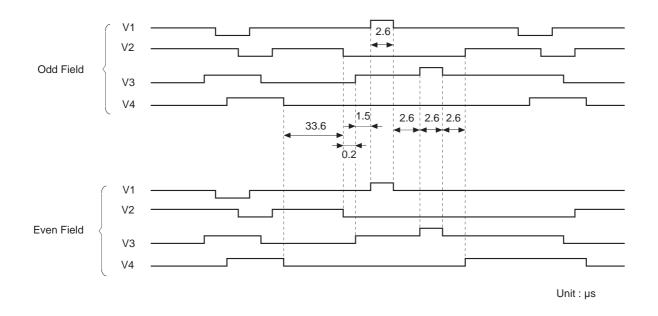


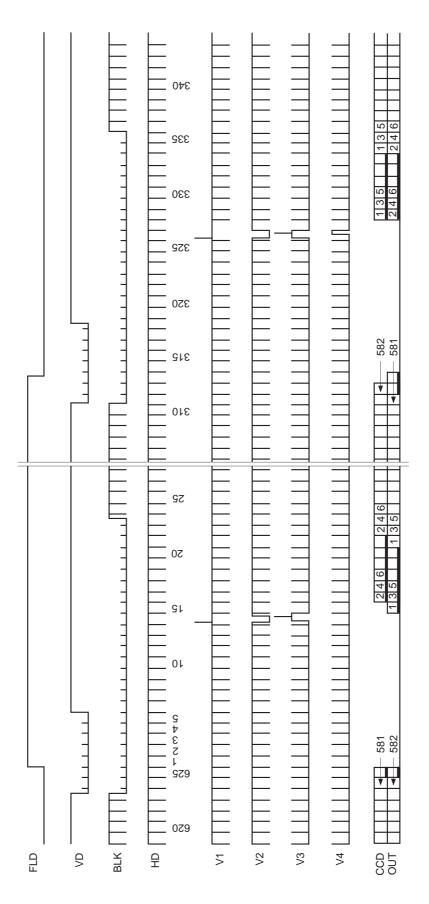
## **Spectral Sensitivity Characteristics**

(excludes both lens characteristics and light source characteristics)

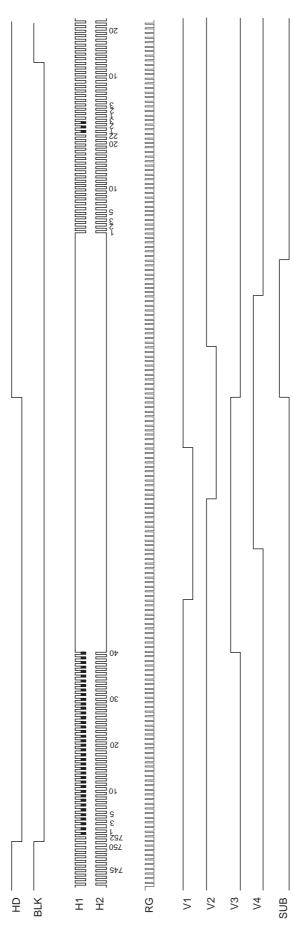


## **Sensor Readout Clock Timing Chart**









## **Notes on Handling**

### 1) Static charge prevention

CCD image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.

- a) Either handle bare handed or use non-chargeable gloves, clothes or material. Also use conductive shoes.
- b) When handling directly use an earth band.
- c) Install a conductive mat on the floor or working table to prevent the generation of static electricity.
- d) Ionized air is recommended for discharge when handling CCD image sensor.
- e) For the shipment of mounted substrates, use boxes treated for the prevention of static charges.

#### 2) Soldering

- a) Make sure the package temperature does not exceed 80°C.
- b) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a ground 30W soldering iron and solder each pin in less than 2 seconds. For repairs and remount, cool sufficiently.
- c) To dismount an image sensor, do not use a solder suction equipment. When using an electric desoldering tool, use a thermal controller of the zero cross On/Off type and connect it to ground.

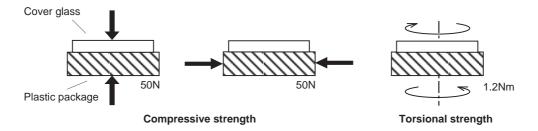
### 3) Dust and dirt protection

Image sensors are packed and delivered by taking care of protecting its glass plates from harmful dust and dirt. Clean glass plates with the following operation as required, and use them.

- a) Perform all assembly operations in a clean room (class 1000 or less).
- b) Do not either touch glass plates by hand or have any object come in contact with glass surfaces. Should dirt stick to a glass surface, blow it off with an air blower. (For dirt stuck through static electricity ionized air is recommended.)
- c) Clean with a cotton bud and ethyl alcohol if the grease stained. Be careful not to scratch the glass.
- d) Keep in a case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.
- e) When a protective tape is applied before shipping, just before use remove the tape applied for electrostatic protection. Do not reuse the tape.

#### 4) Installing (attaching)

a) Remain within the following limits when applying a static load to the package. Do not apply any load more than 0.7mm inside the outer perimeter of the glass portion, and do not apply any load or impact to limited portions. (This may cause cracks in the package.)

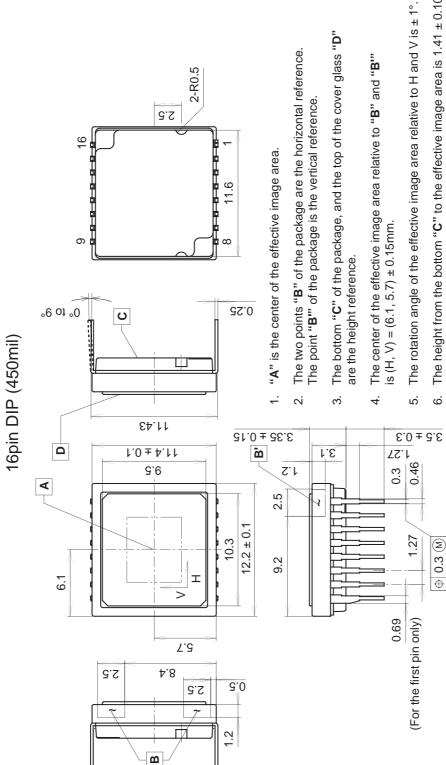


- b) If a load is applied to the entire surface by a hard component, bending stress may be generated and the package may fracture, etc., depending on the flatness of the bottom of the package. Therefore, for installation, use either an elastic load, such as a spring plate, or an adhesive.
- c) The adhesive may cause the marking on the rear surface to disappear, especially in case the regulated voltage value is indicated on the rear surface. Therefore, the adhesive should not be applied to this area, and indicated values should be transferred to the other locations as a precaution.
- d) The notch of the package is used for directional index, and that can not be used for reference of fixing. In addition, the cover glass and seal resin may overlap with the notch of the package.
- e) If the lead bend repeatedly and the metal, etc., clash or rub against the package, the dust may be generated by the fragments of resin.
- f) Acrylate anaerobic adhesives are generally used to attach CCD image sensors. In addition, cyanoacrylate instantaneous adhesives are sometimes used jointly with acrylate anaerobic adhesives. (reference)

### 5) Others

- a) Do not expose to strong light (sun rays) for long periods. For continuous using under cruel condition exceeding the normal using condition, consult our company.
- b) Exposure to high temperature or humidity will affect the characteristics. Accordingly avoid storage or usage in such conditions.
- c) The brown stain may be seen on the bottom or side of the package. But this does not affect the CCD characteristics.
- d) This CCD image sensor has sensitivity in the near infrared area. Its focus may not match in the same condition under visible light /near infrared light because of aberration. Incident light component of long wavelength which transmits the silicon substrate may have bad influence upon image.

Package Outline Unit: mm



PACKAGE STRUCTURE

PACKAGE MATERIAL	Plastic
LEAD TREATMENT	GOLD PLATING
LEAD MATERIAL	42 ALLOY
PACKAGE WEIGHT	0.9g

0mm.	ea is 1.94 ± 0.15mm.	50 m
) height from the bottom "C" to the effective image area is 1.41 $\pm$ 0.10mm.	height from the top of the cover glass "D" to the effective image area is 1.94 $\pm$ 0.15mm.	tilt of the effective image area relative to the bottom "C" is less than 5011m
heigh	heigh	tit of

- . The tilt of the effective image area relative to the bottom "C" is less than 50µm. The tilt of the effective image area relative to the top "D" of the cover glass is less than 50µm.
- 8. The thickness of the cover glass is 0.75mm, and the refractive index is 1.5.
- The notches on the bottom of the package are used only for directional index, they must not be used for reference of fixing.